

Substitute for form 1449A/PTO

(use as many sheets as necessary)

Complete if Known

Application Number

Filing Date

First Named Inventor

Michael J. Rendon

Group Art Unit

Examiner Name

Sheet

1

of

2

Attorney Docket Number

SC11814TP

U. S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

Examiner Signature		Date Considered	6/14/03
-----------------------	---	--------------------	---------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation, if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English Language Translation is attached.

+

Please type a plus sign (+) inside this box. FORM PTO/SB/08

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				<i>Complete if Known</i>	
				Application Number	
				Filing Date	
				First Named Inventor	
				Group Art Unit	
				Michael J. Rendon	
				Examiner Name	
Sheet	2	of	2	Attorney Docket Number	
				SC11814TP	

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
<i>D</i>	AC	Cheolmin Park et al., "50nm SOI CMOS Transistors with Ultra Shallow Junction using Laser Annealing and Pre-Amorphization Implantation",	
<i>D</i>	AD	Jung-Ho Lee et al., "Laser Thermal Annealed SSR well Prior to Epi-channel Growth (LASPE) for 70 nm nFETs", 2000 IEEE, IEDM 00-441, pgs. 18.4.1 – 18.4.4.	
<i>D</i>	AE	Ken-ichi Goto et al., "Ultra-Low Contact Resistance for Deca-nm MOSFETs by Laser Annealing", 1999 IEEE, IEDM-931-IEDM-933, pgs. 20.7.1 – 20.7.3.	
<i>D</i>	AF	Somit Talwar et al., "Ultra-Shallow, Abrupt, and Highly-Activated Junctions by Low-Energy Ion Implantation and Laser Annealing", 1999 IEEE, pgs. 1171-1174.	
<i>D</i>	AG	A. Sato et al., "Determination of Solid Solubility Limit of In and Sb in Si using Bonded Silicon-On-Insulator (SOI) Substrate, Proc. IEEE 1995 Int. Conference on Microelectronic Test Structures, Vol. 8, March 1995, pgs. 259-260.	
<i>D</i>	AH	Bin Yu et al., "70nm MOSFET with Ultra-Shallow, Abrupt, and Super-Doped S/D Extension Implemented by Laser Thermal Process (LTP), 1999 IEEE, IEDM 99-509 – 99-512, pgs. 20.4.1 – 20.4.4.	

Examiner Signature		Date Considered	6/16/03
--------------------	---	-----------------	---------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation, if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² Applicant is to place a check mark here if English Language Translation is attached.